

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising, above a substrate:  
a data ~~lines~~-line extending in a first direction;  
a scanning ~~lines~~-line extending in a second direction and intersecting the data ~~lines~~line;  
a pixel ~~electrodes~~-electrode and a thin film ~~transistors~~-transistor disposed so as to correspond to an intersection ~~regions~~-region of the data ~~lines~~-line and the scanning ~~lines~~line; and  
a storage ~~capacitors~~-capacitor electrically connected to the thin film ~~transistors~~transistor and the pixel ~~electrodes~~electrode, and  
a light-blocking shield layer disposed above the thin film transistor at a position between the data line and the pixel electrode, the light-blocking shield layer covering the data line and including a lower layer formed from aluminum and an upper layer formed from titanium nitride;  
wherein the thin film ~~transistors including~~transistor includes a semiconductor ~~layers~~-layer having a channel ~~regions~~-region that extends in a longitudinal direction and a channel adjacent ~~regions~~-region that further extend-extends from the channel ~~regions~~-region in the longitudinal direction, and  
the scanning ~~line including~~line includes a light-shielding ~~parts~~-part disposed at sides-a side of the channel ~~regions~~-region.

2. (Currently Amended) The electro-optical device according to Claim 1, further comprising:

a shielding layers-layer disposed between the data ~~lines-line~~ and the pixel ~~electrodeselectrode~~.

3. (Currently Amended) The electro-optical device according to Claim 1, the scanning ~~lines-line~~ including a main-body parts-part extending in a direction ~~which-that~~ intersects the longitudinal direction and a gate electrodes-electrode of the thin film ~~transistors transistor~~ overlapped with the channel ~~regions-region~~ in plan view, and a horizontal protrusions-protrusion protruding from the main-body ~~parts-part~~ at the ~~sides-side~~ of the channel region in the longitudinal direction in plan view and constituting a light-shielding part.

4. (Currently Amended) The electro-optical device according to Claim 3, ~~each-of~~ the main-body ~~parts-part~~ and ~~each-of~~ the horizontal ~~protrusions-protrusion~~ being integrally formed of the same film.

5. (Currently Amended) The electro-optical device according to Claim 3, the horizontal ~~protrusions-protrusion~~ protruding from source and drain sides of the channel ~~regions-region~~ in plan view.

6. (Currently Amended) The electro-optical device according to Claim 1, the thin film ~~transistors-transistor~~ including a semiconductor layers-layer having a channel regions-which extendregion that extends in a longitudinal direction,

~~wherein~~ the electro-optical device, further comprising:

an upper light-shielding films-film at least covering the channel ~~regions-region~~ of the thin film ~~transistors-transistor~~ from the upper side, and

at least a part of ~~each of the~~ upper light-shielding ~~films~~ film being formed in a concave shape in a cross section perpendicular to the longitudinal direction of the channel ~~regions~~ region as viewed from the channel ~~regions~~ region.

7. (Withdrawn; Currently Amended) The electro-optical device according to Claim 1, the thin film ~~transistors~~ transistor including a semiconductor layers layer having a channel regions which extend region that extends in the first direction, and

the scanning ~~lines~~ line including a main-line parts part including a gate electrodes electrode of the thin film ~~transistors~~ transistor which face transistor that faces the channel ~~regions~~ region with a gate insulating films film interposed therebetween and extending in the second direction intersecting the first direction in plan view, and a surrounding parts which extend part that extends to surround the semiconductor ~~layers~~ layer from the main-line ~~parts~~ part at ~~positions~~ which area position that is separated from the channel ~~regions~~ region by a predetermined distance in the second direction in plan view.

8. (Withdrawn; Currently Amended) The electro-optical device according to Claim 7, the scanning ~~lines~~ line further including a vertical protrusions which protrude protrusion that protrudes from the surrounding ~~parts~~ part in a vertical direction to the substrate.

9. (Currently Amended) The electro-optical device according to Claim 1, the thin film ~~transistors~~ transistor including a semiconductor layers layer having a channel regions which extend region that extends in the first direction, and

the scanning ~~lines~~ line including a main-line parts part including the gate ~~electrodes~~ electrode of the thin film ~~transistors~~ transistor which face transistor that faces the channel ~~regions~~ region with the gate insulating ~~films~~ film interposed therebetween and extending in the second direction intersecting the first direction in plan view, and a vertical protrusions which protrude protrusion that protrudes downwardly from the main-line ~~parts~~ part at

~~positions which are~~ a position that is separated from the channel ~~regions-region~~ by a predetermined distance in the second direction in plan view.

10. (Currently Amended) An electro-optical device according to Claim 9, further comprising:

above the substrate, a lower light-shielding films-film covering at least the channel ~~regions-region~~ from the lower ~~sides-side~~ thereof,

the vertical ~~protrusions-protrusion~~ contacting the lower light-shielding ~~films-film~~ at a front endsend.

11. (Currently Amended) The electro-optical device according to Claim 9, further comprising:

above the substrate, a lower light-shielding films-film covering at least the channel ~~regions-region~~ from the lower ~~sides-side~~ thereof,

the vertical ~~protrusions-protrusion~~ not contacting the lower light-shielding ~~films-film~~ at the front ~~endsend~~.

12. (Currently Amended) The electro-optical device according to Claim 1, the thin film ~~transistors-transistor~~ including a semiconductor layers-layer having a channel regions-which extendregion that extends in the first direction,

the scanning ~~lines-line~~ including the main-line ~~parts-part~~ including the gate ~~electrodes-electrode~~ of the thin film ~~transistors-which face~~ transistor that faces the channel ~~regions-region~~ with the gate insulating ~~films-film~~ interposed therebetween and extending in the second direction intersecting the first direction in plan view, and

the main-line ~~parts-part~~ being disposed inside ~~grooves-a groove~~ engraved in the substrate and including an inside-groove parts-which coverpart that covers at least a part of the channel ~~regions-region~~ from the ~~sides-side~~ thereof.

13. (Currently Amended) The electro-optical device according to Claim 1, the scanning ~~lines~~line including a light-shielding ~~films~~film containing metal or alloy.

14. (Currently Amended) The electro-optical device according to Claim 1, one of a pair of electrodes constituting ~~each of the storage eapaeitors~~capacitor constituting a part of a capacitive line formed along the second direction, and

the capacitive line being made of a multi-layered film including a low-resistive film.

15. (Currently Amended) The electro-optical device according to Claim 1, the pixel ~~electrodes~~electrode being electrically connected to an other ~~layers~~layer of a laminated structure through a titanium simple substance, a tungsten simple substance, a compound of titanium and tungsten, or a stack thereof.

16. (Currently Amended) The electro-optical device according to Claim 15, the laminated structure further including an interlayer insulating ~~films~~film provided as ~~bases~~a base of the pixel ~~electrodes~~electrode,

a contact ~~holes~~hole being formed in the interlayer insulating ~~films~~film to electrically connect the pixel ~~electrodes~~electrode thereto, and

~~films~~a film being formed as at least an inside ~~surfaees~~surface of the contact ~~holes~~hole and a lower ~~layers~~layer of the pixel ~~electrodes~~electrode, the ~~films~~film including a titanium simple substance, a tungsten simple substance, a compound of titanium or tungsten, or a stack thereof.

17. (Currently Amended) The electro-optical device according to Claim 1, wherein the data ~~lines~~beingline is formed of the same film as one of a pair of electrodes which constitute ~~each of the storage eapaeitors~~capacitor.

18. (Currently Amended) The electro-optical device according to Claim 2, further comprising:

a ~~relay layers-layer~~ as a part of a laminated structure, the ~~relay layers-layer~~ electrically connecting ~~each of the pixel electrodes-electrode~~ to one of a pair of electrodes which constitute ~~each of the storage capacitorscapacitor~~.

19. (Currently Amended) The electro-optical device according to Claim 18, the shielding ~~layers-layer~~ being formed of the same ~~films-film~~ as the ~~relay layers-layer~~.

20. (Currently Amended) The electro-optical device according to Claim 2, at least some elements of the scanning ~~linesline~~, the data ~~linesline~~, a pair of electrodes constituting ~~each of the storage capacitorscapacitor~~, and the shielding ~~layers-layer~~ being made of light-shielding material, and

at least some elements thereof constitute an embedded light-shielding film in the laminated structure.

21. (Currently Amended) The electro-optical device according to Claim 1, further comprising:

the light-shielding ~~films-film~~ being disposed in the light-shielding regions,  
the light-shielding ~~films-film~~ including a metal ~~layers-which containlayer~~ that contains a high-melting-point metal simple substance or metal ~~compoundscompound~~, and a barrier ~~layers-which arelayer~~ that is made of a high-melting-point and oxygen-free metal or metal ~~compoundscompound~~ laminated on at least one surface of the metal ~~layers-layer~~.

22. (Currently Amended) The electro-optical device according to Claim 21, the metal ~~layers-layer~~ of the light-shielding ~~films-film~~ including a light-shielding metal ~~layers-layer~~ and light-absorption metal ~~layers-layer~~,

the light-absorption metal ~~layers-layer~~ facing the thin film ~~transistorstransistor~~.

23. (Currently Amended) The electro-optical device according to Claim 21, ~~each~~  
~~of the metal layers-layer~~ being interposed between the barrier layers.

24. (Currently Amended) The electro-optical device according to Claim 21, the  
light-shielding ~~films-film~~ being set at ~~a fixed potentialspotential~~.

25. (Currently Amended) An electro-optical device comprising, above a substrate:  
a data lines-line extending in a first direction;  
a scanning lines-extendingline that extends in a second direction and  
~~intersecting-intersects~~ the data ~~linesline~~;

a pixel electrodes-electrode and thin film ~~transistors-transistor~~ disposed so as  
to correspond to an intersection regions-region of the data ~~lines-line~~ and the scanning  
~~linesline~~;

a storage capaeiters-capacitor electrically connected to the thin film ~~transistors~~  
~~transistor~~ and the pixel ~~electrodeselectrode~~; and

a light-shielding films-film disposed between the data ~~lines-line~~ and the pixel  
~~electrodeselectrode~~, the light-blocking shield layer covering the data line and including a  
lower layer formed from aluminum and an upper layer formed from titanium nitride,

the thin film ~~transistors-transistor~~ including a semiconductor layers-layer  
having a channel regions-which extendregion that extends in a longitudinal direction and a  
channel adjacent ~~regions-whichregion that~~ further ~~extend-extends~~ from the channel ~~regions~~  
region in the longitudinal direction, and

the scanning ~~lines-line~~ including a light-shielding parts-part disposed at ~~sides-a~~  
side of the channel ~~regionsregion~~.

26. (Currently Amended) An electronic apparatus comprising an electro-optical device comprising, above a substrate:

a data ~~lines~~ ~~line~~ extending in a first direction;

a scanning ~~lines~~ ~~line~~ extending in a second direction and intersecting the data ~~lines~~ line;

a pixel ~~electrodes~~ ~~electrode~~ and thin film ~~transistors~~ transistor disposed so as to correspond to an intersection ~~regions~~ ~~region~~ of the data ~~lines~~ line and the scanning ~~lines~~ line; and

a storage ~~capacitors~~ ~~capacitor~~ electrically connected to the thin film ~~transistors~~ transistor and the pixel ~~electrodes~~ electrode, and

a light-blocking shield layer disposed above the thin film transistor at a position between the data line and the pixel electrode, the light-blocking shield layer covering the data line and including a lower layer formed from aluminum and an upper layer formed from titanium nitride,

the thin film ~~transistors~~ transistor including a semiconductor ~~layers~~ ~~layer~~ having a channel ~~regions~~ ~~which extend~~ ~~region~~ that extends in a longitudinal direction and a channel adjacent ~~regions~~ ~~which~~ ~~region~~ that further extend extends from the channel ~~regions~~ region in the longitudinal direction, and

the scanning ~~lines~~ line including a light-shielding ~~parts~~ ~~part~~ disposed at ~~sides~~ a side of the channel ~~regions~~ region.